100mA / 50V Digital transistors (with built-in resistors)

DTA114EB / DTA114EM / DTA114EE / DTA114EUA / DTA114EKA

●Applications

Inverter, Interface, Driver

●Features

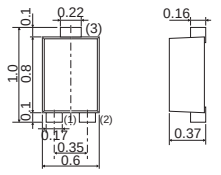
1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
3) Only the on/off conditions need to be set for operation, making the device design easy.

●Structure

PNP epitaxial planar silicon transistor (Resistor built-in type)

●Dimensions (Unit : mm)

DTA114EB



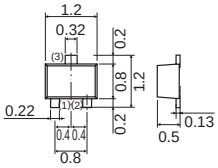
(1) IN
(2) GND
(3) OUT

Each lead has same dimensions

ROHM : **VMN3**

Abbreviated symbol : 14

DTA114EM



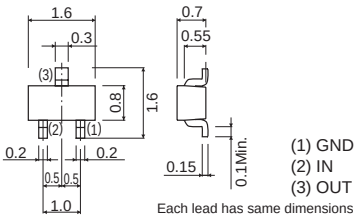
(1) IN
(2) GND
(3) OUT

Each lead has same dimensions

ROHM : VMT3

Abbreviated symbol : 14

DTA114EE



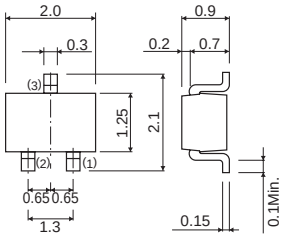
(1) GND
(2) IN
(3) OUT

Each lead has same dimensions

ROHM : EMT3

Abbreviated symbol : 14

DTA114EUA



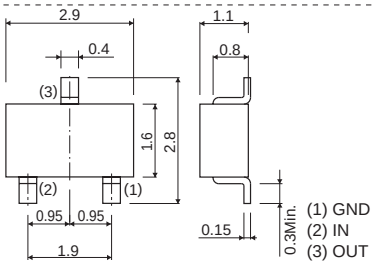
(1) GND
(2) IN
(3) OUT

Each lead has same dimensions

ROHM : UMT3
EIAJ : SC-70

Abbreviated symbol : 14

DTA114EKA



(1) GND
(2) IN
(3) OUT

Each lead has same dimensions

ROHM : SMT3
EIAJ : SC-59

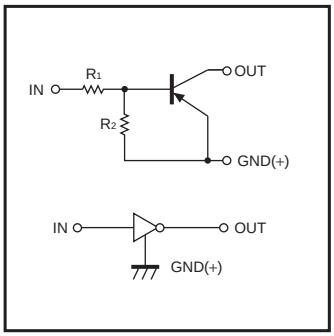
Abbreviated symbol : 14

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●Packaging specifications

Type	Package	VMN3	VMT3	EMT3	UMT3	SMT3
	Packaging type	Taping	Taping	Taping	Taping	Taping
	Code	T2L	T2L	TL	T106	T146
	Basic ordering unit (pieces)	8000	8000	3000	3000	3000
DTA114EB		○	–	–	–	–
DTA114EM		–	○	–	–	–
DTA114EE		–	–	○	–	–
DTA114EUA		–	–	–	○	–
DTA114EKA		–	–	–	–	○

●Equivalent circuit



R_1=R_2=10kΩ

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits					Unit
		DTA114EB	DTA114EM	DTA114EE	DTA114EUA	DTA114EKA	
Supply voltage	V_{CC}	–50					V
Input voltage	V_{IN}	–40 to +10					V
Output current	I_O	–50					mA
	$I_{C(Max.)}$	–100					
Power dissipation	Pd	150			200		mW
Junction temperature	Tj	150					°C
Storage temperature	Tstg	–55 to +150					°C

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	$V_{I(off)}$	–	–	–0.5	V	V_{CC}=–5V, I_O=–100μA
	$V_{I(on)}$	–3	–	–		V_O=–0.3V, I_O=–10mA
Output voltage	$V_{O(on)}$	–	–	–0.3	V	I_O/I_I=–10mA/–0.5mA
Input current	I_I	–	–	–0.88	mA	V_I=–5V
Output current	$I_{O(off)}$	–	–	–0.5	μA	V_{CC}=–50V, V_I=0V
DC current gain	G_I	30	–	–	–	V_O=–5V, I_O=–5mA
Input resistance	R_1	7	10	13	kΩ	–
Resistance ratio	R_2/R_1	0.8	1	1.2	–	–
Transition frequency	f_T*	–	250	–	MHz	V_{CE}=–10V, I_E=5mA, f=100MHz

* Characteristics of built-in transistor

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●Electrical characteristic curves

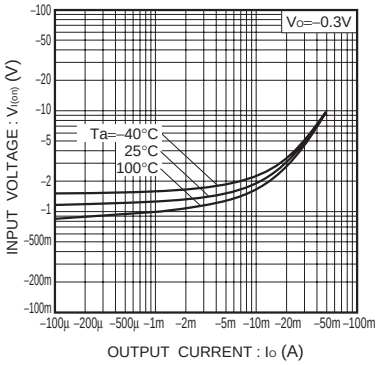


Fig.1 Input voltage vs. output current (ON characteristics)

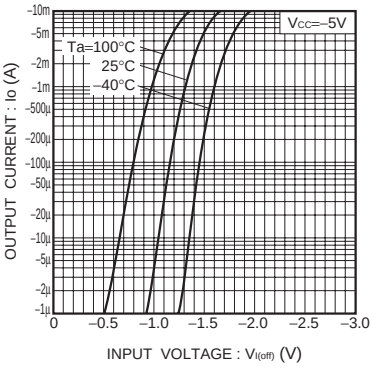


Fig.2 Output current vs. input voltage (OFF characteristics)

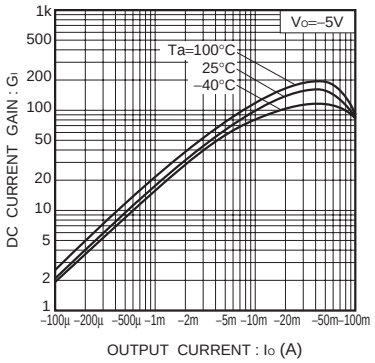


Fig.3 DC current gain vs. output current

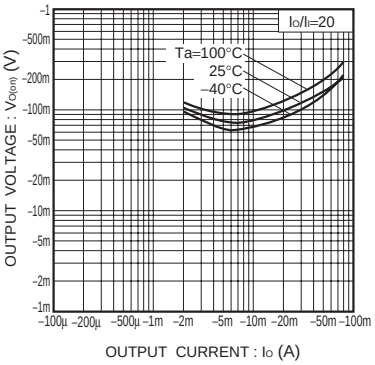


Fig.4 Output voltage vs. output current

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